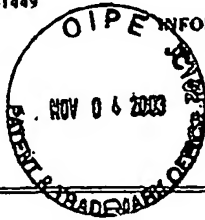


Form PTO-1449


**INFORMATION DISCLOSURE CITATION  
IN AN APPLICATION**  
(Use several sheets if necessary)

Docket Number (Optional)

068758.0102

Application Number

09786832

10/633044

Applicant

Deboy et al.

Filing Date

04/22/99

Group Art Unit:

**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE
PK	3,171,068	02/23/65	Denkewalter et al.	317	234	10/19/60
	3,925,803	12/09/75	Kobayashi	357	22	07/12/73
	3,961,356	06/01/76	Okuhara et al.	357	50	10/31/74
	4,003,072	01/11/77	Matsushita et al.	357	52	11/01/74
	4,055,884	11/01/77	Jambotkar	29	571	12/13/76
	4,072,975	02/07/78	Ishitani	357	23	04/22/77
	4,101,922	07/18/78	Tihanyi	357	23	03/09/77
	4,145,700	03/20/79	Jambotkar	357	23	08/08/77
	4,320,410	03/16/82	Nishizawa et al.	357	43	05/03/79
	4,345,265	08/17/82	Blanchard	357	23	04/14/80
	4,366,495	12/28/82	Goodman et al.	357	23	08/06/79
	4,376,286	03/08/83	Lidow et al.	357	23	02/09/81
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	Translation YES NO
	EP 0 053 854 B1	16.06.82	EPO	H01L	29/06	x
	GB 2 089 118 A	16.02.82	UK	H01L	29/78	x
	EP 0 069 429 A2	12.01.83	EPO	H01L	29/78	x
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EXAMINER

DATE CONSIDERED

7/16/04

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP §609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

Form PTO-1449

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IN AN APPLICATION**  
(Use several sheets if necessary)

Docket Number (Optional)

068758.0102

Application Number

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10/633044

Applicant Deboy et al.

Filing Date 04/22/99

Group Art Unit:

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE
<i>RA</i>	4,404,575	09/13/83	Nishizawa	357	22	05/03/82
	4,417,385	11/29/83	Temple	29	571	09/09/82
	4,561,003	12/24/85	Tihanyi et al.	357	23.4	04/13/84
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	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	Translation YES NO
	EP 0 772 244 A1	07.05.97	EPO	H01L	29/78	x
	DE 196 04 043 A1	5.2.96	Germany	H01L	29/78	x
	WO 97/29518	14.08.97	PCT	H01L	29/78	x
	DE 196 04 044 A1	5.2.97	Germany	H01L	29/78	x
	WO 97/35346	25.09.97	PCT	H01L	29/78	x
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(Including Author, Title, Date, Pertinent Pages, Etc.)

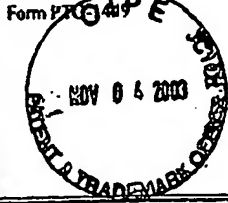
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EXAMINER

DATE CONSIDERED

7/16/04

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Docket Number (Optional)

068758.0102

Application Number

09/286,022

10/633 044

Applicant Deboy et al.

Filing Date 04/22/99

Group Art Unit:

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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE	
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	4,926,226	05/15/90	Heremans et al.	357	27	09/06/88	
	4,941,026	07/10/90	Temple	357	23.4	08/26/88	
	4,974,059	11/27/90	Kinzer	357	23.4	08/28/89	
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	5,089,434	02/18/92	Hollinsner	437	41	01/22/90	
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						YES	NO
	WO99/36961	22.07.99	PCT	H01L	23/48		x
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	WO 00/14807	16.03.00	PCT	H01L	29/78		x
	DE 198 40 032 C1	2.9.98	Germany	H01L	29/78		x
	WO 99/62123	02.12.99	PCT	H01L	29/861		x
	DE 198 23 944 A1	28.5.98	Germany	H01L	29/861		x

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(Including Author, Title, Date, Pertinent Pages, Etc.)

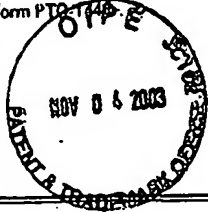
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EXAMINER

DATE CONSIDERED

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**INFORMATION DISCLOSURE CITATION  
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Docket Number (Optional)

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004380,022

10/633046

Applicant Deboy et al.

Filing Date 04/22/99

Group Art Unit:

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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE	
Pg	5,126,807	06/30/92	Baba et al.	357	23.4	06/12/91	
	5,182,234	01/26/93	Meyer	437	233	07/26/91	
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	5,438,215	08/01/95	Tihyani	257	401	03/25/94	
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	WO 00/02250	13.01.00	PCT	H01L	29/10		x
	EP 0 973 203 A2	19.01.00	EPO	H01L	29/06		x
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	IEEE	1980	Victor K. Temple, Robert P. Love, Peter V. Gray: "A 600-Volt MOSFET Designed for Low On-Resistance" (p 343-349)
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DATE CONSIDERED

7/16/04

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058758.0102

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00786022-

10/633044

Applicant Deboy et al.

Filing Date 04/22/99

Group Art Unit:

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE
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DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	Transition	
					YES	NO

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(Including Author, Title, Date, Pertinent Pages, Etc.)

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EXAMINER

DATE CONSIDERED

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**INFORMATION DISCLOSURE CITATION  
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**Patent Office**  
NOV 06 2003

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068758.0102

**Application Number**  
004986322  
10/633084

**Applicant** Deboy et al.

**Filing Date** 04/22/99

**Group Art Unit:**

**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	Translation YES NO

**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

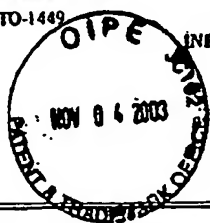
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			Article from Chinese Journal of Semiconductors, May 1988 (p 255-260)

**EXAMINER** *John Shah*

**DATE CONSIDERED** 7/16/04

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Form PTO-1449



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## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	<div> <div>Translative</div> <div>YES NO</div> </div>

## OTHER DOCUMENTS


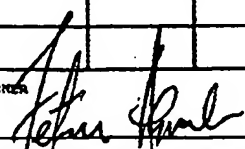
(Including Author, Title, Date, Pertinent Pages, Etc.)

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EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with AUPP §609; Draw line through citation if not in conformance and not considered. Include copy of this form with own communication to the applicant.

Form PTO-1449 				INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)		DocId Number (Optional) 068758.0102		Application Number 090786033- 10/633049	
						Applicant Deboy et al.			
						Filing Date 04/22/99		Group Art Unit:	
U.S. PATENT DOCUMENTS									
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE			
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	Translated YES NO			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)									
P <sub>2</sub>		1998	Lorenz et al. article, "Improved MOSFET An Important Milestone Toward a New Power MOSFET Generation" featured in PCIM						
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EXAMINER 				DATE CONSIDERED 2/15/04					
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